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APPLICATION NO. FILING DATE		FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	O. CONFIRMATION NO.		
09/452,691	12/02/1999	FRED D. BAILEY	TI-27935	1638		
23494	7590 07/02/2003					
TEXAS INSTRUMENTS INCORPORATED			EXAMI	EXAMINER		
P O BOX 655474, M/S 3999 DALLAS, TX 75265			FENTY, JESSE A			
			ART UNIT	PAPER NUMBER		
			2815			

Please find below and/or attached an Office communication concerning this application or proceeding.

DATE MAILED: 07/C2/2003

PTO-90C (Rev. 07-01)

0		Application No.		Applicant(s)	M			
		09/452,691		BAILEY ET AL.				
Office Action Summary		Examiner	A					
	•	· ·	lM)	Art Unit	•			
	Th MAILING DATE of this communication app	Jesse A. Fenty	sheet with the c	2815 orrespondence add	ress			
Period for Reply								
THE II - Exter after - If the - If NO - Failur - Any r	ORTENED STATUTORY PERIOD FOR REPLY MAILING DATE OF THIS COMMUNICATION. Insions of time may be available under the provisions of 37 CFR 1.1 SIX (6) MONTHS from the mailing date of this communication. In period for reply specified above is less than thirty (30) days, a reply period for reply is specified above, the maximum statutory period to reply within the set or extended period for reply will, by statute eply received by the Office later than three months after the mailing and patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, howe y within the statutory min will apply and will expire , cause the application to	ever, may a reply be tim nimum of thirty (30) days SIX (6) MONTHS from to become ABANDONE	nely filed s will be considered timely. the mailing date of this con O (35 U.S.C. § 133).	nmunication.			
1)🖂	Responsive to communication(s) filed on 04 A	A <i>pril 2003</i> .						
2a)⊠		is action is non-fi	nal.					
3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213. Disposition of Claims								
4)⊠ Claim(s) <u>1-8,17 and 18</u> is/are pending in the application.								
4a) Of the above claim(s) is/are withdrawn from consideration.								
5) Claim(s) is/are allowed.								
6)⊠	6)⊠ Claim(s) <u>1-8, 17 and 18</u> is/are rejected.							
7) Claim(s) is/are objected to.								
8) Claim(s) are subject to restriction and/or election requirement.								
Application	on Papers							
	The specification is objected to by the Examine							
10)☐ The drawing(s) filed on is/are: a)☐ accepted or b)☐ objected to by the Examiner.								
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).								
11) ☐ The proposed drawing correction filed on is: a) ☐ approved b) ☐ disapproved by the Examiner.								
If approved, corrected drawings are required in reply to this Office action.								
12) The oath or declaration is objected to by the Examiner.								
Priority u	nder 35 U.S.C. §§ 119 and 120							
13)	Acknowledgment is made of a claim for foreign	priority under 35	5 U.S.C. § 119(a))-(d) or (f).				
a) ☐ All b) ☐ Some * c) ☐ None of:								
	1. Certified copies of the priority documents have been received.							
	2. Certified copies of the priority documents have been received in Application No							
 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received. 								
	cknowledgment is made of a claim for domesti		•		opplication).			
a)	☐ The translation of the foreign language procknowledgment is made of a claim for domesti	visional application	on has been rece	eived.	, r			
Attachment		-	••					
2) Notice	e of References Cited (PTO-892) e of Draftsperson's Patent Drawing Review (PTO-948) nation Disclosure Statement(s) (PTO-1449) Paper No(s)	4)		(PTO-413) Paper No(s) atent Application (PTO-				
J.S. Patent and Tra PTO-326 (Rev		ion Summary		Part of Paper No. 16				

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DETAILED ACTION

Claim Rejections - 35 USC § 102

1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in a patent granted on an application for patent by another filed in the United States before the invention thereof by the applicant for patent, or on an international application by another who has fulfilled the requirements of paragraphs (1), (2), and (4) of section 371(c) of this title before the invention thereof by the applicant for patent.

The changes made to 35 U.S.C. 102(e) by the American Inventors Protection Act of 1999 (AIPA) do not apply to the examination of this application as the application being examined was not (1) filed on or after November 29, 2000, or (2) voluntarily published under 35 U.S.C. 122(b). Therefore, this application is examined under 35 U.S.C. 102(e) prior to the amendment by the AIPA (pre-AIPA 35 U.S.C. 102(e)).

2. Claims 1-3, 6, 7, 17 and 18 are rejected under 35 U.S.C. 102(e) as being anticipated by Saia et al. (U.S. Patent No. 5,874,770).

In re claims 1 and 17, Saia discloses a semiconductor device, comprising:

A lower metal interconnect layer (46) located over a semiconductor body (45);

A multi-level dielectric layer (42, 10, 40) located over said lower interconnect layer;

An upper metal interconnect layer (47) located over said multi-level dielectric layer; and

A thin film resistor (28) embedded within said multi-level dielectric layer between and physically separated in a vertical direction from said lower metal interconnect layer and said upper metal interconnect layer.

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Wherein said thin film resistor is physically separated in a vertical direction from any metal interconnect layer.

In re claim 2, Saia discloses the devices of claim 1, further comprising:

A first via (47) extending from said upper metal interconnect layer to said lower interconnect layer; and

A second via (via filled by conductive regions 21 and 50) extending from said upper metal layer to said thin film resistor.

In re claim 3, Saia discloses the device of claim 1, wherein said thin film resistor comprises a top plate which can be used as a hard mask (MacElwee; column 7, lines 48-51, teaches the use of a top electrode plate as a hard mask.)

In re claim 6, Saia discloses the device of claim 1, wherein said thin film resistor structure comprises TaN (column 5, line 7).

In re claim 7, Saia discloses the device of claim 1, wherein said thin film resistor structure comprises SiCr (column 5, line 9).

In re claim18, Saia discloses the device of claim17, further comprising:

A first plurality of conductively filled vias (47) extending from said upper metal interconnect layer to said lower interconnect layer; and

A second plurality of conductively filled vias (21, 52) extending from said upper metal layer to said thin film resistor.

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1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claim Rejections - 35 USC § 103

2. Claims 4, 5 and 8 are rejected under 35 U.S.C. 103(a) as being unpatentable over Saia et al. as applied to claim 1 above, and further in view of Linn et al. (U.S. Patent No. 5,547,896).

In re claims 4 and 5, Saia discloses the device of claim 3, wherein the resistor comprises chromium silicide (column 5, line 9) with a masking layer but does not expressly disclose a "hard mask" layer comprising TiW or TiN. Linn et al. (Figs. 1a-3b) discloses an electrode of the same material overlaid by a TiW or TiN "hard mask." It would have been obvious to one skilled in the art at the time of the invention to use a hard mask as taught by Linn to overlay the chromium electrode of Saia for the purpose, for example, of cleanly etching a chromium alloy resistor such that residual contaminants will not compromise the integrity of the chromium resistor (Linn; column 1, lines 60-66; column 2, lines 26-30).

In re claim 8, Saia discloses the device of claim 3, but does not expressly disclose the resistor comprising NiCr. Linn discloses a thin film resistor comprising NiCr. It would have been obvious for one skilled in the art at the time of the invention substitute the SiCr resistor of Saia with the NiCr resistor as disclosed by Linn because Linn discloses said materials are "well known" and commonly used thin film transistor structures (column 1, lines 9-13).

Response to Arguments

3. Applicant's arguments filed 4/4/3 have been fully considered but they are not persuasive.

Examiner maintains the Saia rejection, including the new amendments. The rejection to claims 1 and 17 is altered to use the interconnect (47), which overlaps the multi-layer dielectric, as the upper layer interconnect. The reference is re-interpreted in this way to correlate to amended claim 2, that specifies a via extending from the upper level interconnect layer to the lower level interconnect layer.

Amended claim 1 is still anticipated because the resistor (28) disclosed by Saia is "physically separated in a *vertical* direction from any metal interconnect layer." The resistor is vertically separated from the metal layers though perhaps not horizontally.

Conclusion

4. THIS ACTION IS MADE FINAL. Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.

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Any inquiry concerning this communication or earlier communications from the

examiner should be directed to Jesse A. Fenty whose telephone number is 703-308-8137. The

examiner can normally be reached on 5/4-9 1st Fri. Off.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, Eddie Lee can be reached on 703-308-1690. The fax phone numbers for the

organization where this application or proceeding is assigned are 703-308-7722 for regular

communications and 703-746-3892 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding

should be directed to the receptionist whose telephone number is 703-308-0956.

Jesse A. Fenty

Examiner Art Unit 2815

JAF

June 30, 2003

JEROME JACKSON PRIMARY EXAMINER

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